

FIG. 1
PRIOR ART

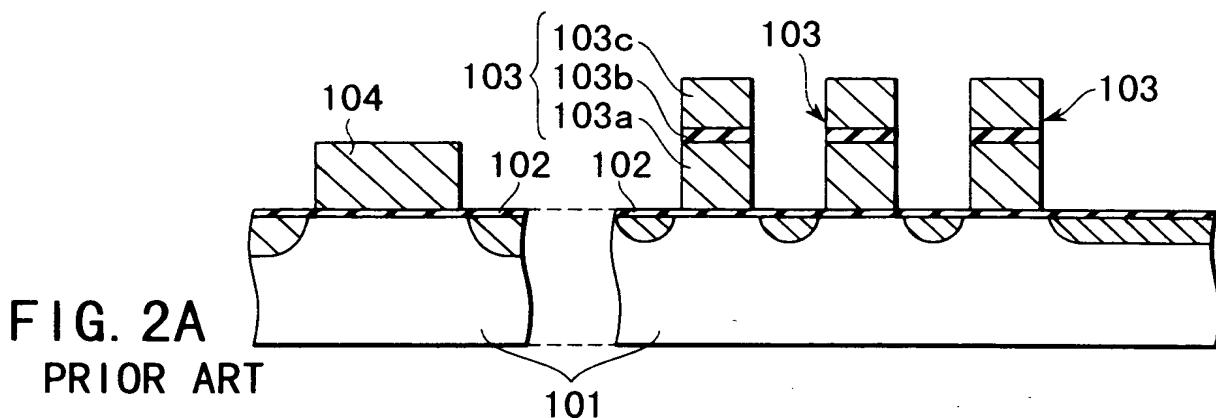


FIG. 2A
PRIOR ART

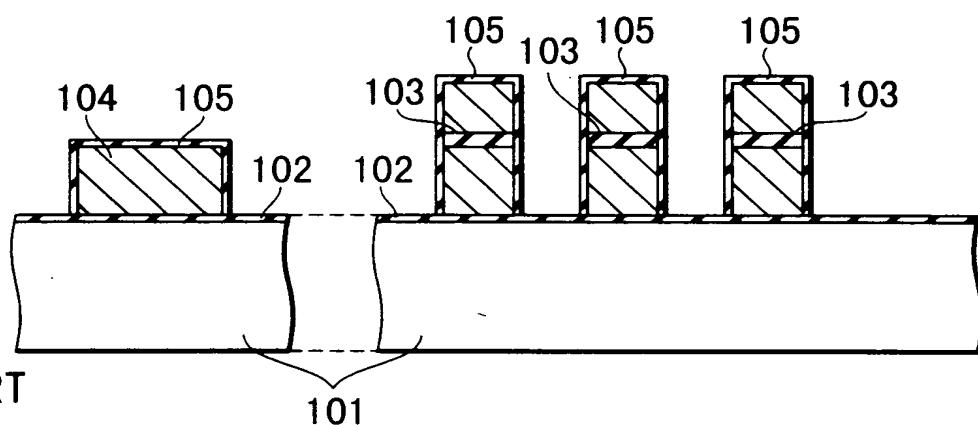


FIG. 2B
PRIOR ART

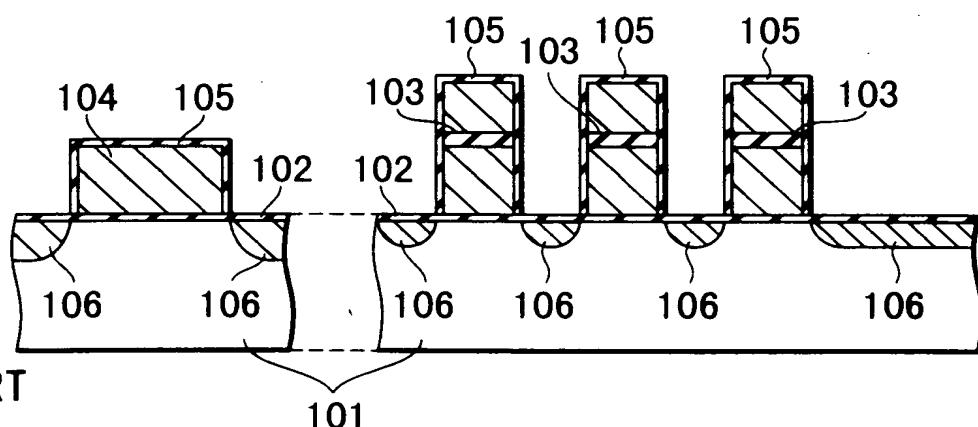


FIG. 2C
PRIOR ART

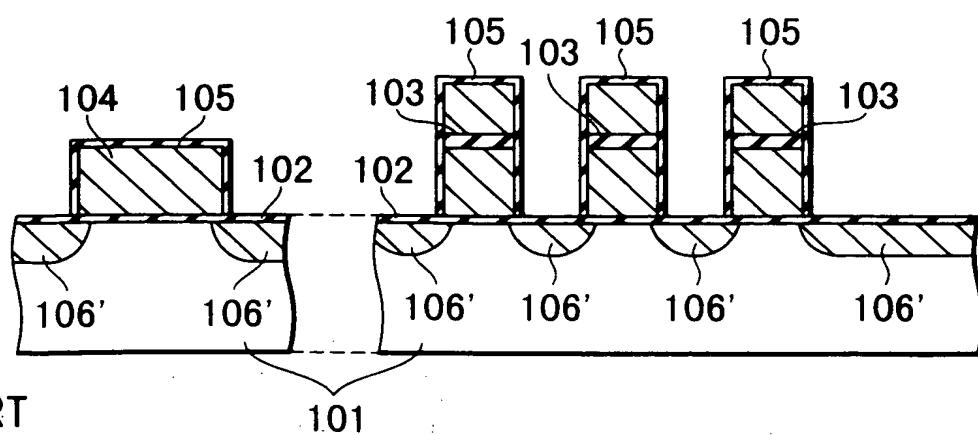


FIG. 2D
PRIOR ART

0039-7692-28 22/2005060

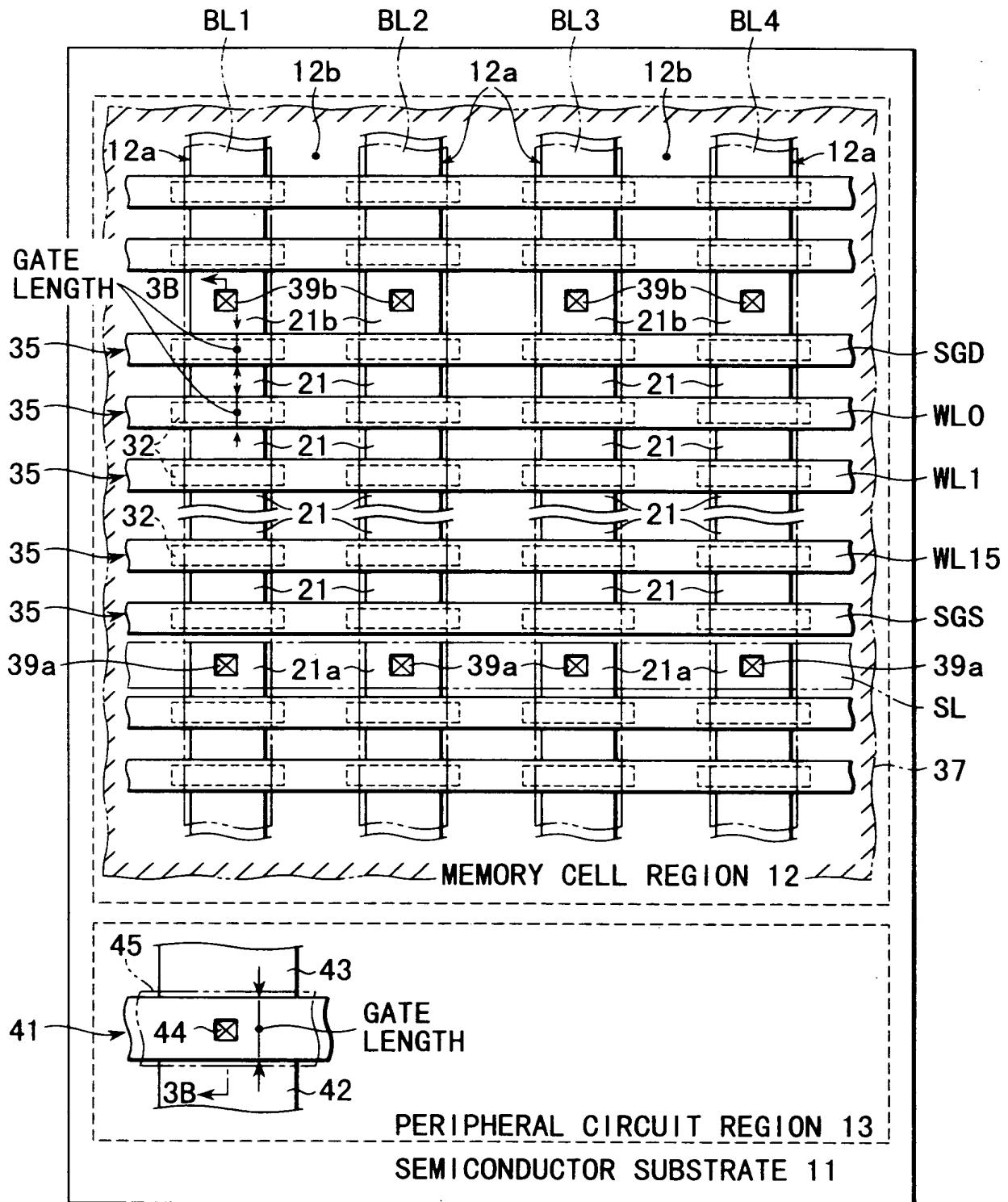


FIG. 3A

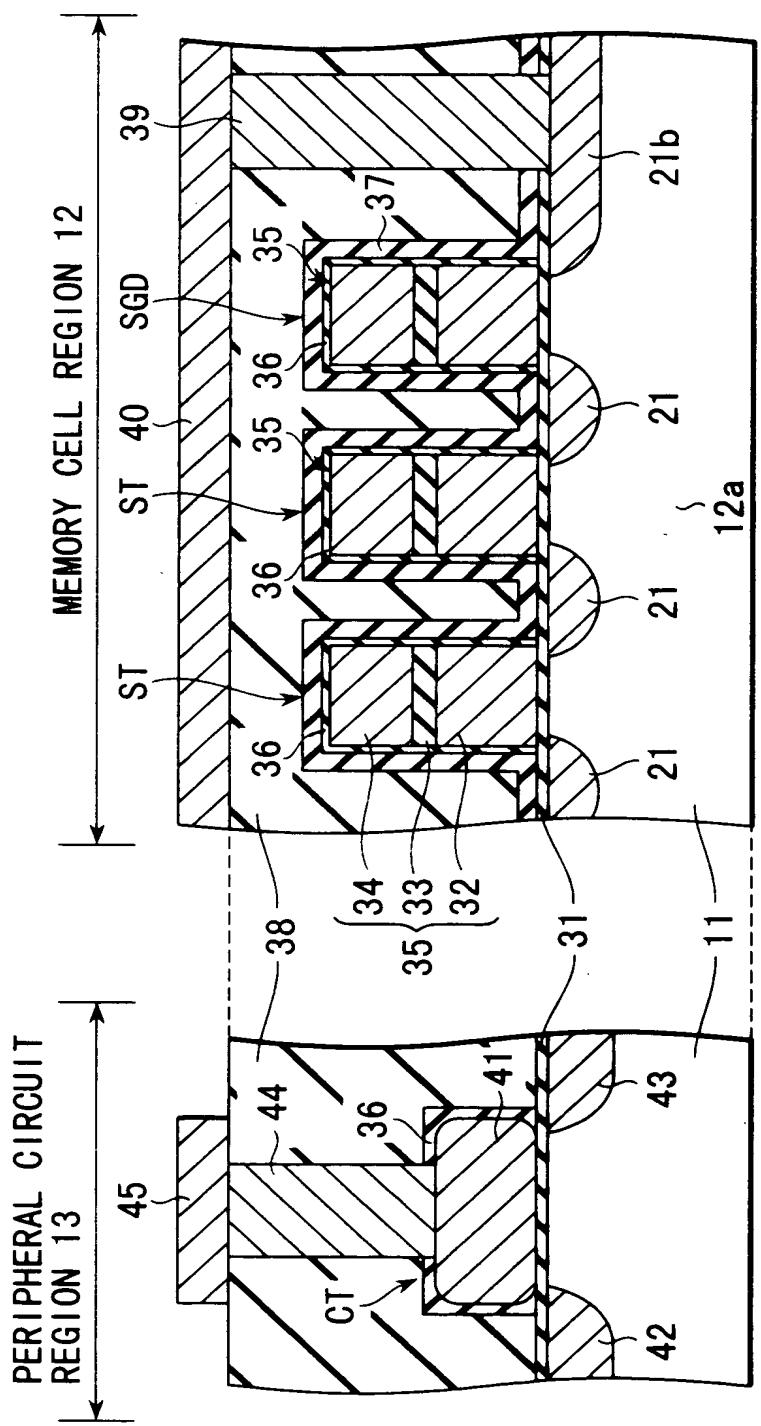


FIG. 3B

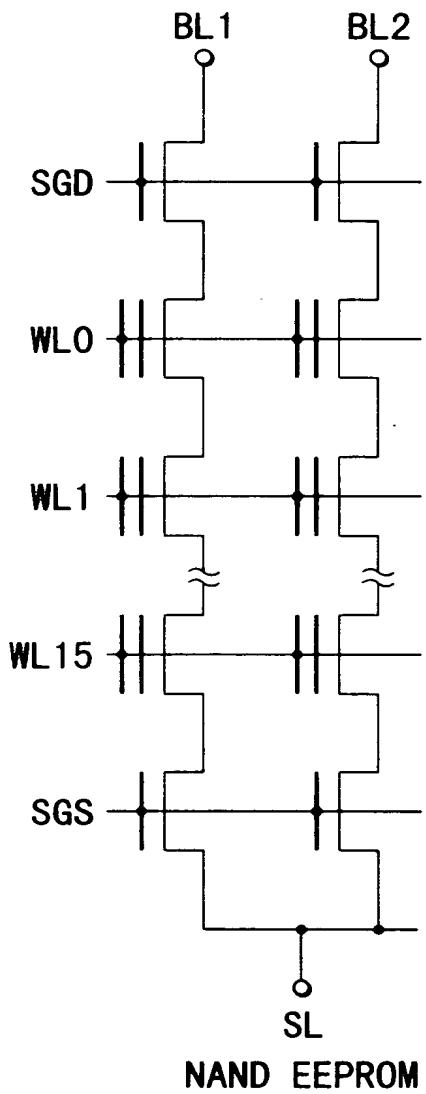
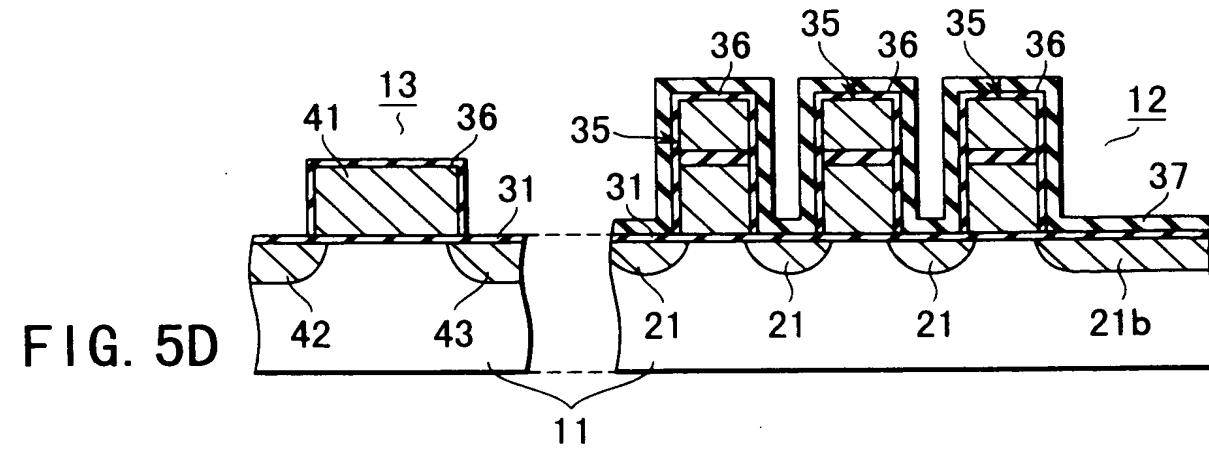
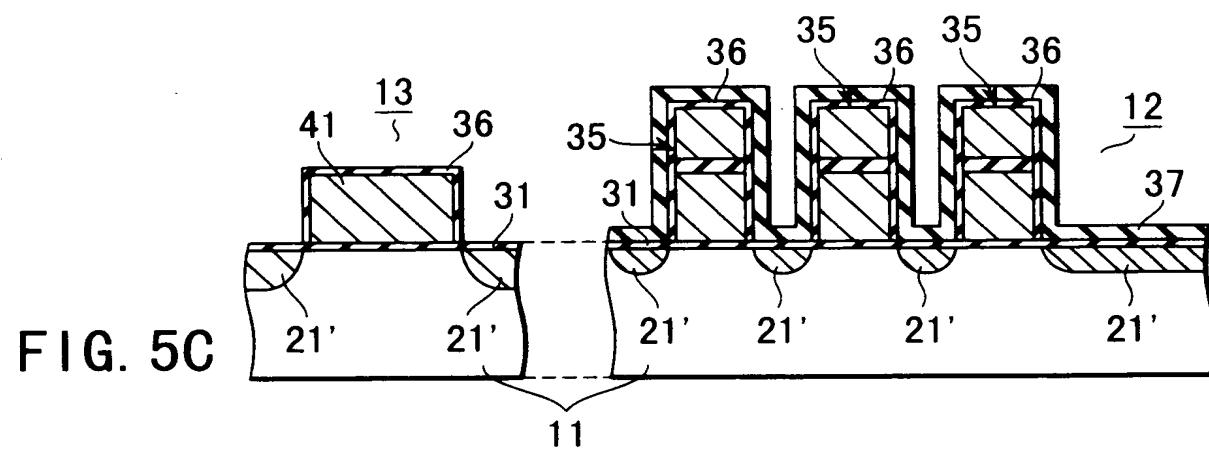
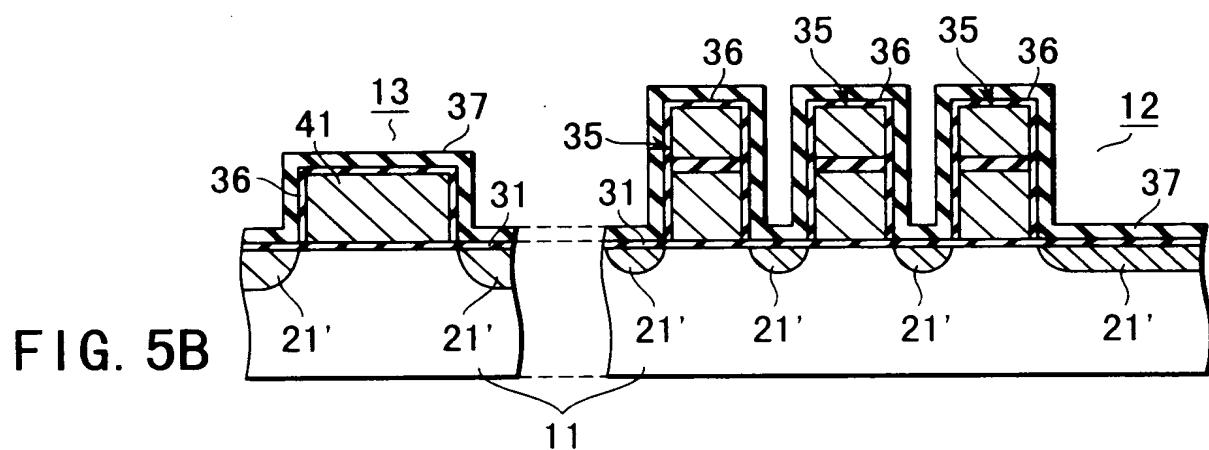
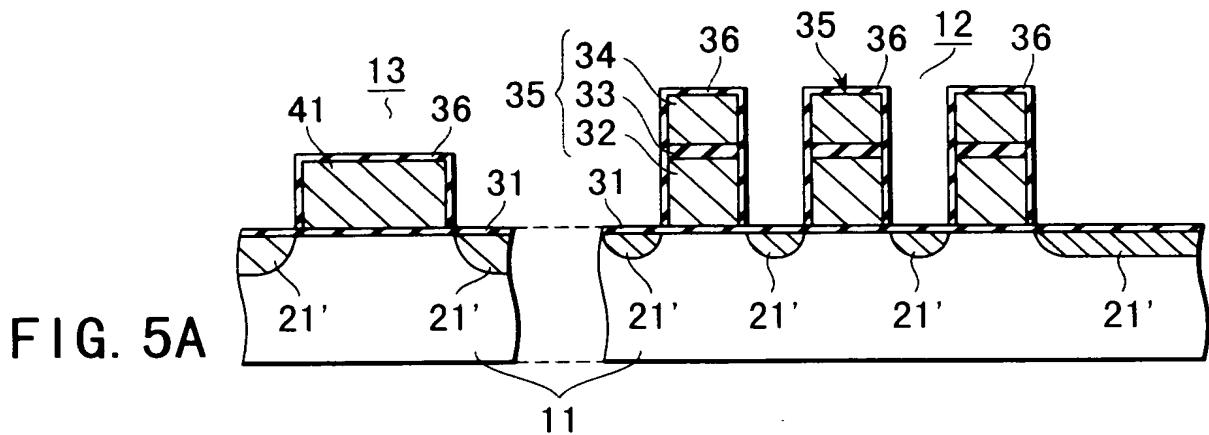


FIG. 4



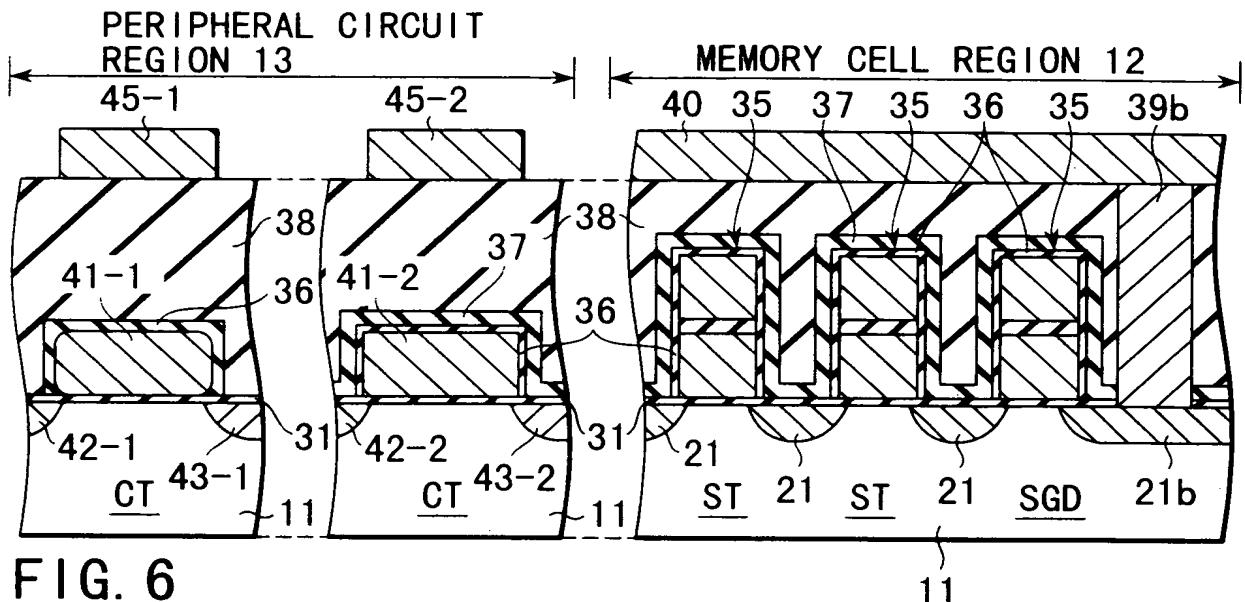


FIG. 6

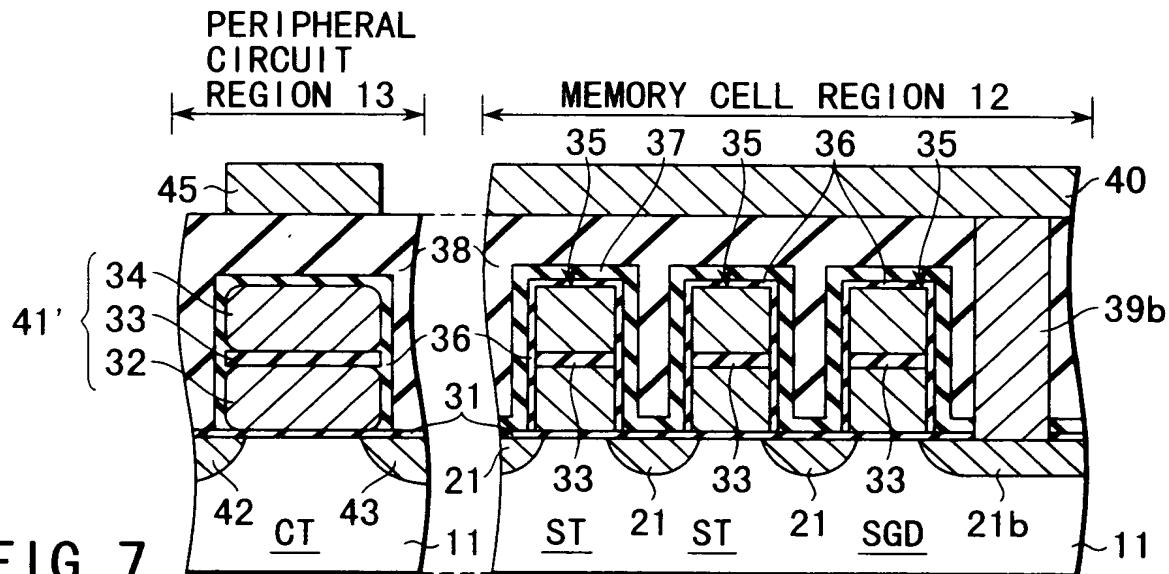


FIG. 7

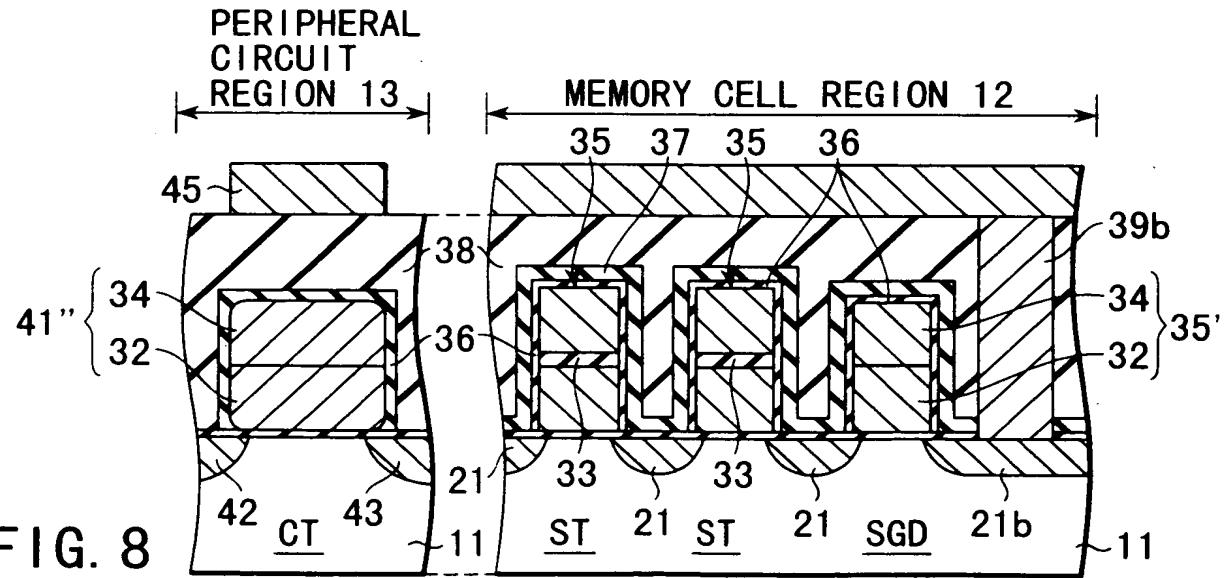


FIG. 8

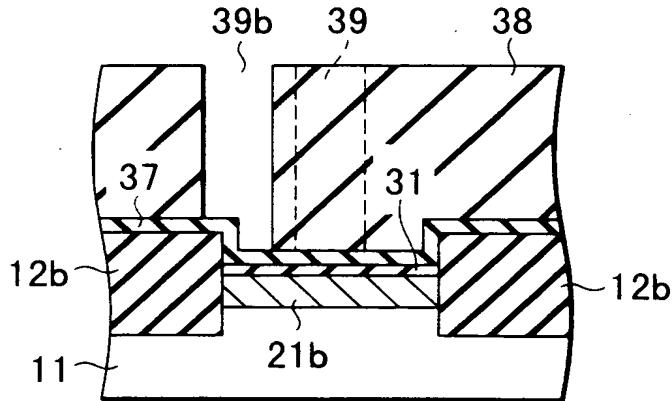


FIG. 9A

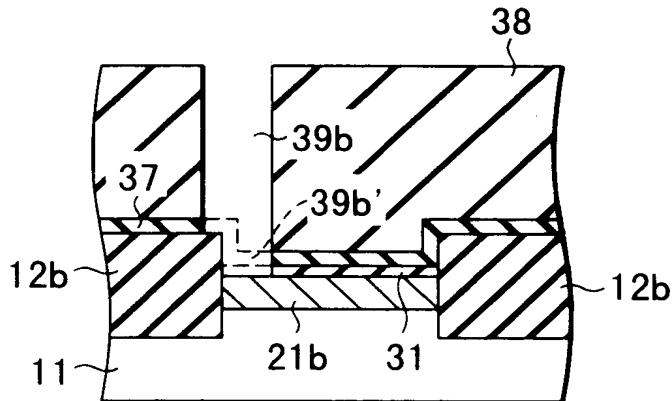


FIG. 9B

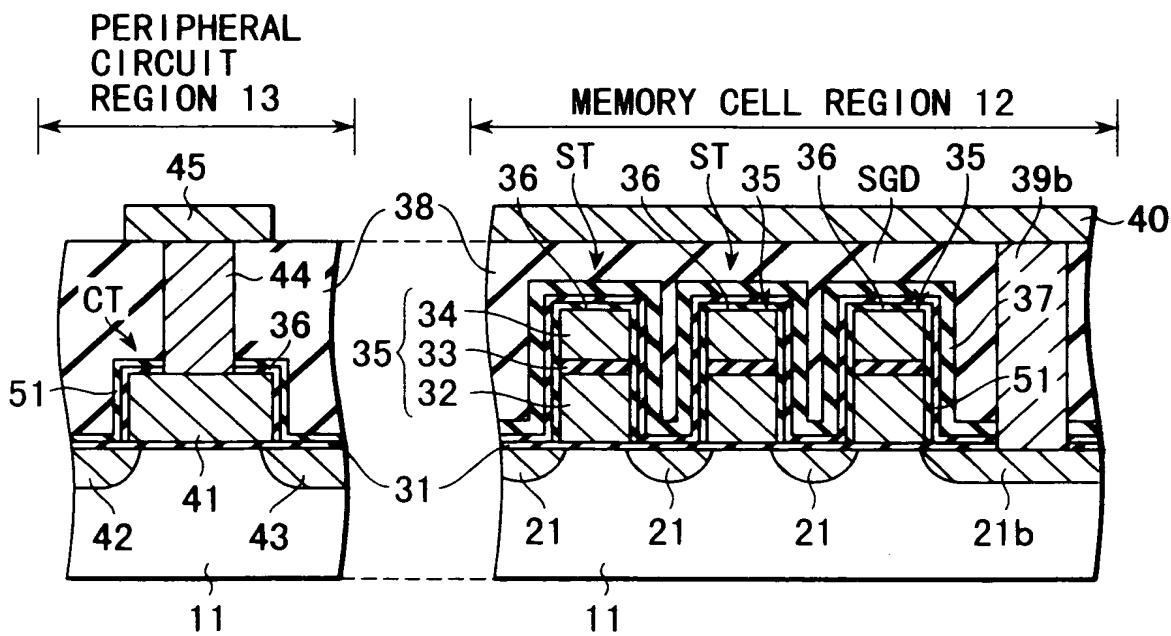


FIG. 12

FIG. 10A

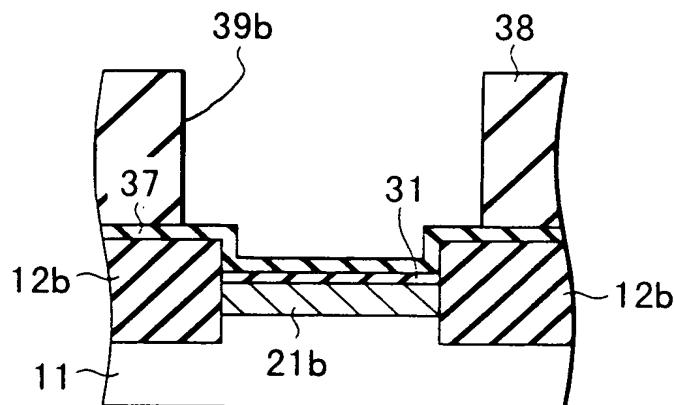
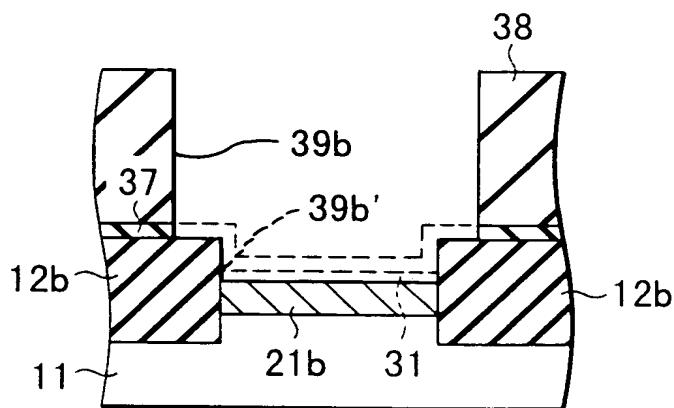


FIG. 10B



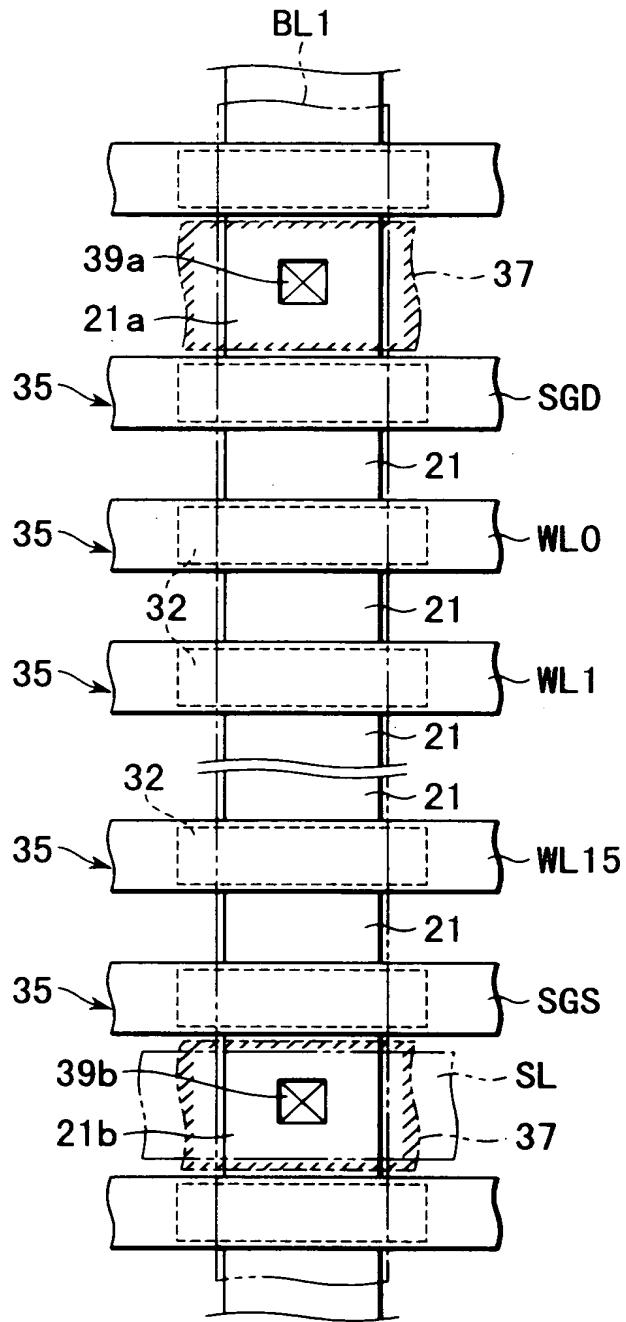


FIG. 11

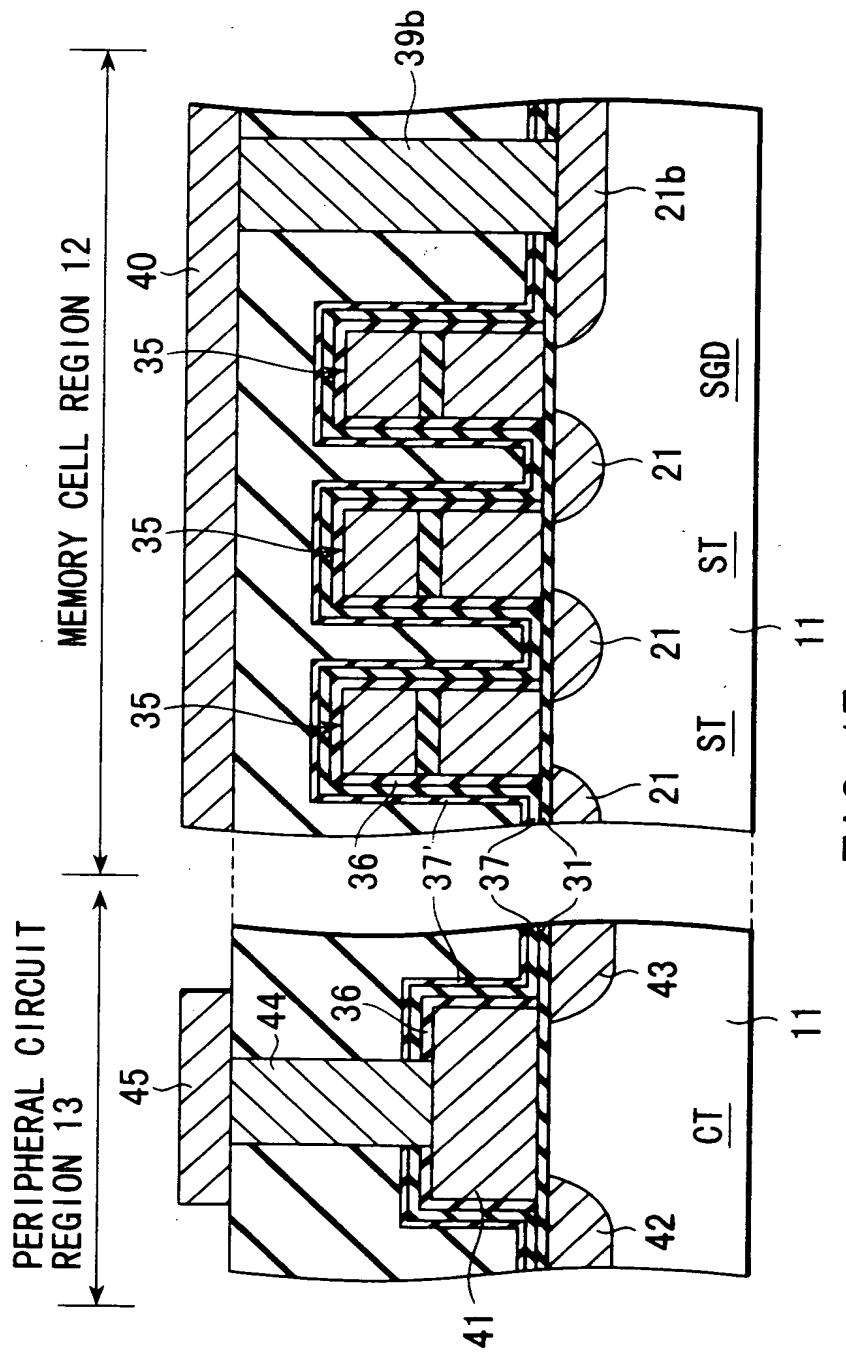
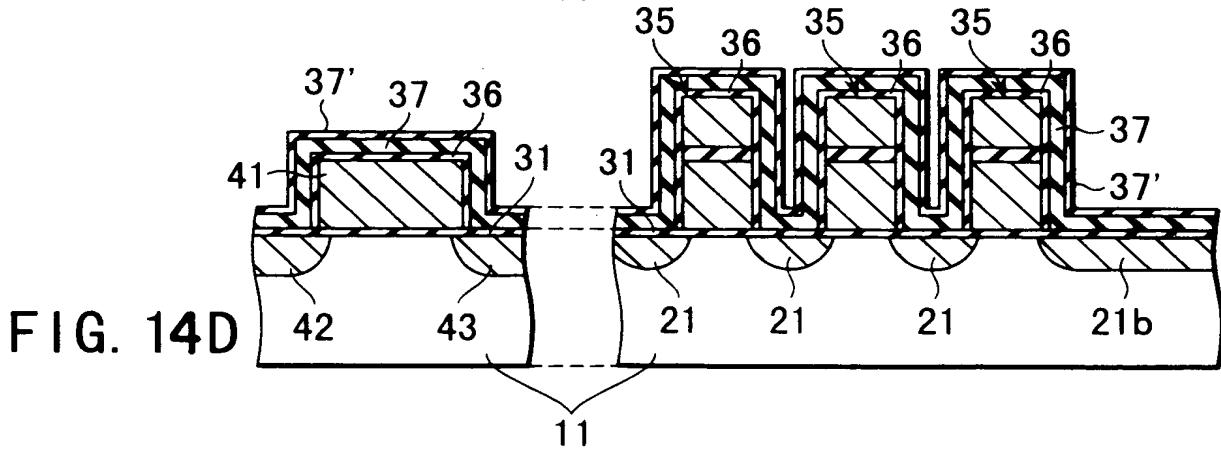
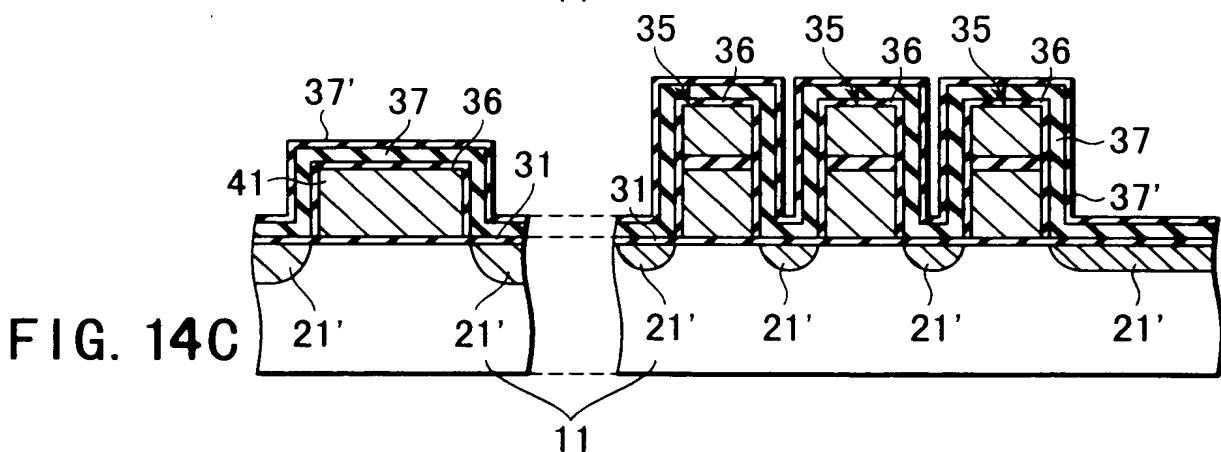
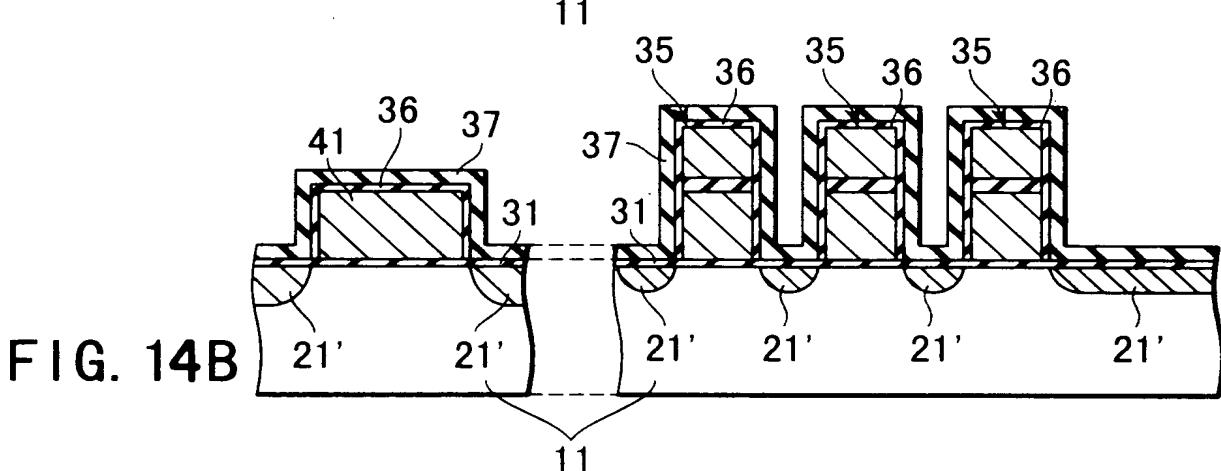
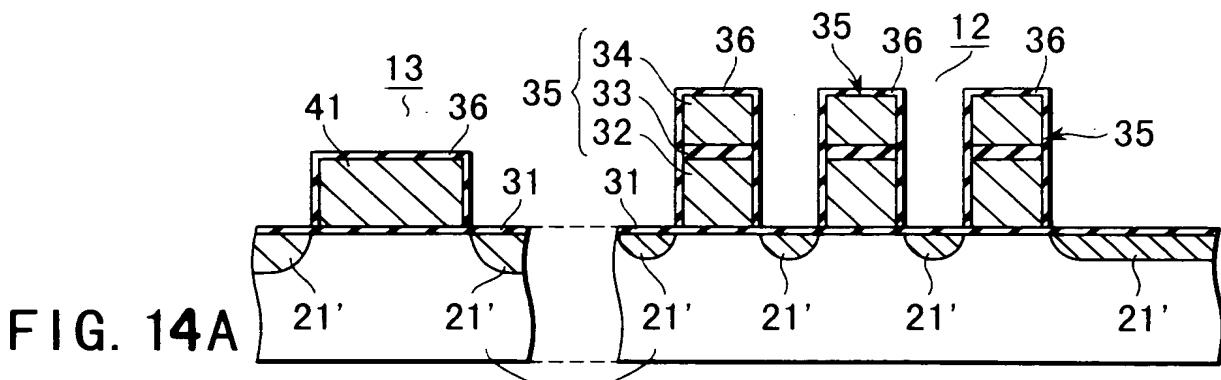
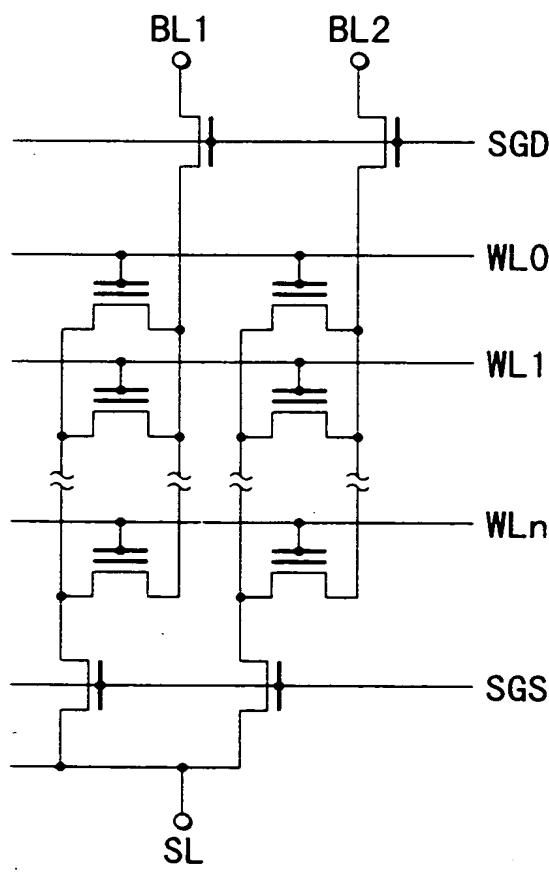


FIG. 13



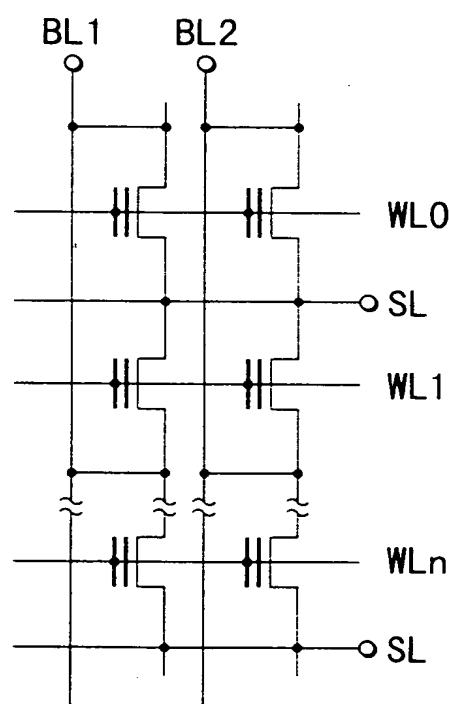
| | CONCENTRATION OF HYDROGEN IN SiN FILM | CONCENTRATION OF HYDROGEN IN TUNNEL OXIDE FILM | dV_g (ELECTRON AMOUNT TRAP) |
|---------------------------------|--|---|-------------------------------------|
| NO SURFACE OXIDE FILM | 4.0×10^{21} atom/cm ³ | 1 | 512mV |
| SURFACE OXIDE FILM FORMED | 1.6×10^{21} atom/cm ³ | 0.2 | 398mV |

FIG. 15



AND EEPROM

FIG. 16A



NOR EEPROM

FIG. 16B